

# SRF520 THRU SRF5200 ( SINGLE CHIP )



SEMICONDUCTOR

## SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts

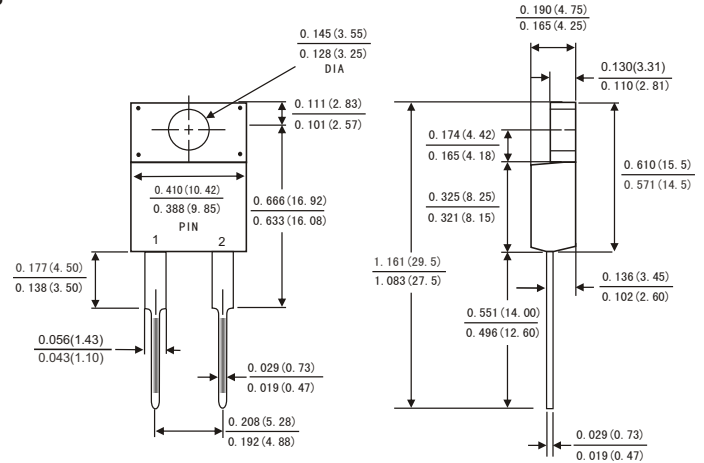
Forward Current - 5.0Amperes

## FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- High temperature soldering guaranteed:260°C/10 seconds, 0.25"(6.35mm)from case
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



## ITO-220AC



## MECHANICAL DATA

- Case: JEDEC ITO-220AC molded plastic body
- Terminals: Lead solderable per MIL-STD-750,method 2026
- Polarity: As marked
- Mounting Position: Any
- Weight: 0.08ounce, 2.24 gram

Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified ,Single phase ,half wave ,resistive or inductive load. For capacitive load,derate by 20%.)

	Symbols	SRF 520	SRF 530	SRF 540	SRF 550	SRF 560	SRF 580	SRF 5A0	SRF 5150	SRF 5200	Units
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	V <sub>RMS</sub>	14	21	28	35	42	57	71	105	140	Volts
Maximum DC blocking voltage	V <sub>DC</sub>	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current 0.375"(9.5mm) lead length(see fig.1)	I(AV)	5.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated T <sub>J</sub> )	I <sub>FSM</sub>	150.0									Amps
Maximum instantaneous forward voltage at 5.0 A(Note 1 )	V <sub>F</sub>	0.60		0.75		0.85		0.90		0.95	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	I <sub>R</sub>	0.5									mA
		50			25						
Typical junction capacitance(Note 3)	C <sub>J</sub>	500			400						pF
Typical thermal resistance (Note 2)	R <sub>θJA</sub>	25.0									°C/W
	R <sub>θJL</sub>	8.0									
Operating junction temperature range	T <sub>J</sub>	-65 to +125			-65 to +150						°C
Storage temperature range	T <sub>STG</sub>	-65 to +150									°C

Notes: 1.Pulse test: 300 μ s pulse width,1% duty cycle

2.Thermal resistance from junction to lead vertical P.C.B. mounted , 0.375"(9.5mm)lead length

3.Measured at 1MHz and reverse voltage of 4.0volts

# RATINGS AND CHARACTERISTIC CURVES SRF520 THRU SRF5200 ( SINGLE CHIP)

FIG.1-FORWARD CURRENT DERATING CURVE

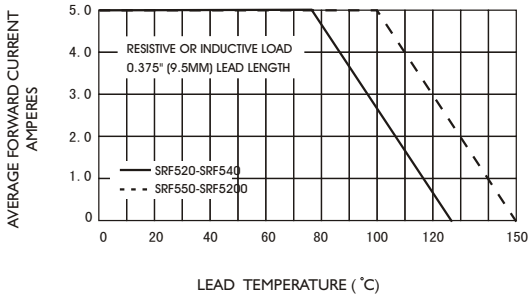


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

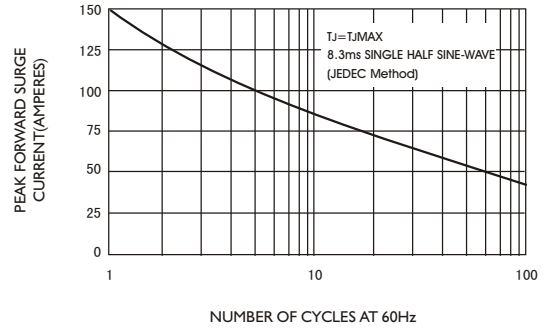


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

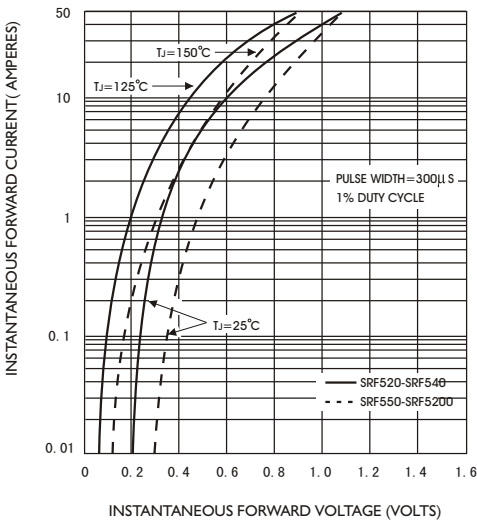


FIG.4-TYPICAL REVERSE CHARACTERISTICS

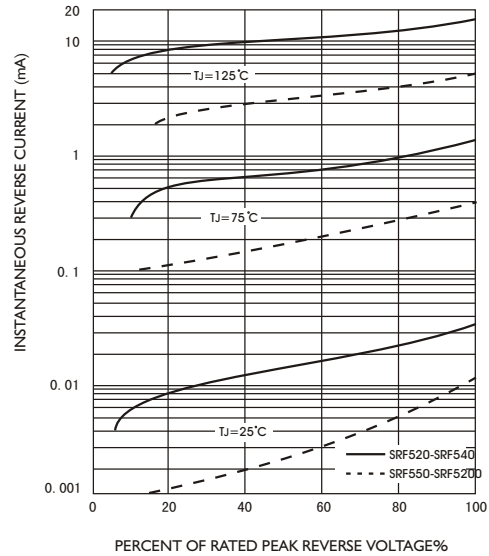


FIG.5-TYPICAL JUNCTION CAPACITANCE

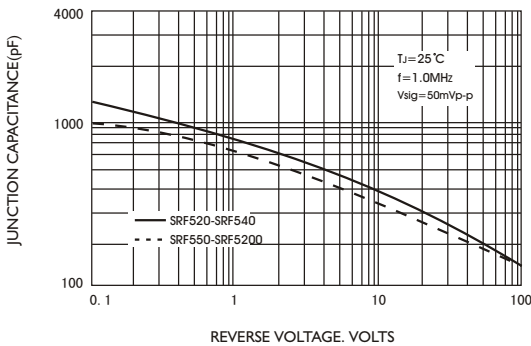


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE

